Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-16. (Canceled)

17. (Currently Amended) A semiconductor device, comprising:

~~a metal-oxide-semiconductor field-effect transistor including:~~

a silicon substrate,

a gate insulation film on the silicon substrate, ~~and~~

~~a gate electrode on the gate insulation film, the gate electrode including~~ a germanium film on the gate insulation film, and

a transition metal silicide in direct contact with the germanium film,

wherein p-type impurities are doped into the germanium film, and a range of concentration of the p-type impurities is about 10^{17} to 10^{20} cm^{-3}.

18. (Previously Presented) The semiconductor device according to claim 17, wherein the germanium film includes at least one of a single-crystalline germanium film, a polycrystalline germanium film and an amorphous germanium film.

19-21. (Canceled)

22. (Currently Amended) A semiconductor device, comprising:

~~a metal-oxide-semiconductor field-effect transistor including:~~

~~a silicon film,~~

a substrate;

~~a~~ an insulation film on the substrate; ~~and~~

a silicon film on the insulation film;

~~a gate electrode on the gate insulation film, the gate electrode including~~ a germanium film on the gate insulation film; and

_____a transition metal silicide in direct contact with the germanium film,_

wherein p-type impurities are doped into the germanium film, and a range of concentration of the p-type impurities is about 10^{17} to 10^{20} cm^{-3}.

23.   (Canceled)

24.   (Previously Presented) The semiconductor device according to claim 22, wherein the germanium film includes at least one of a single-crystalline germanium film, a polycrystalline germanium film and an amorphous germanium film.

25-31. (Canceled)

32.   (New) The semiconductor device according to claim 17, wherein p-type impurities are doped into a channel region, and a range of concentration of the P-type impurities is 10^{17} to 10^{20} cm^{-3}, and wherein a resistance of the substrate is 14 to 22 Ω/cm.